

JIEJIE MICROELECTRONICS CO.

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	2.5	kV
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($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value	Unit	
I	$V_D=12V$ $R_L=33$	- -	MAX.	50A	
V		- -	MAX.	1 V	
V	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	- -	MIN	0.2 V	
I_L	$I_G \leq 2I_{GT}$	-	MAX.	50	mA
				90	
I_H	$I_T \leq 100mA$		MAX.	50	mA
dV/dt	$V_D=800V$ Gate Open $T_j=125$		MIN.	500	V/ μs
(dI/dt) _c	(dV/dt) _c =20V/ μs , T_j				

t_{on} mA @ CH0 TdARACTERIS.

Year _____ J ST 08 C -1200 BW

FIG.1: Maximum power dissipation versus RMS on-state current

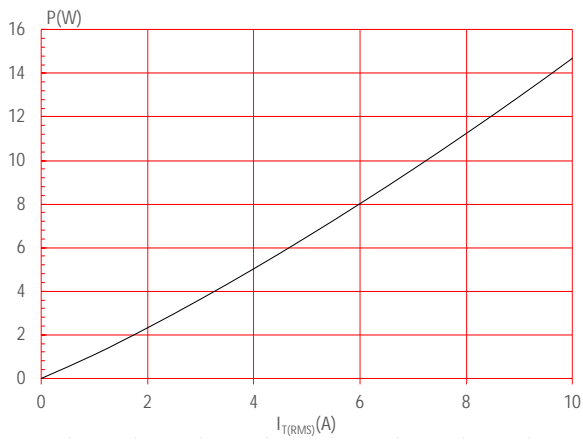


FIG.2: RMS on-state current versus case temperature

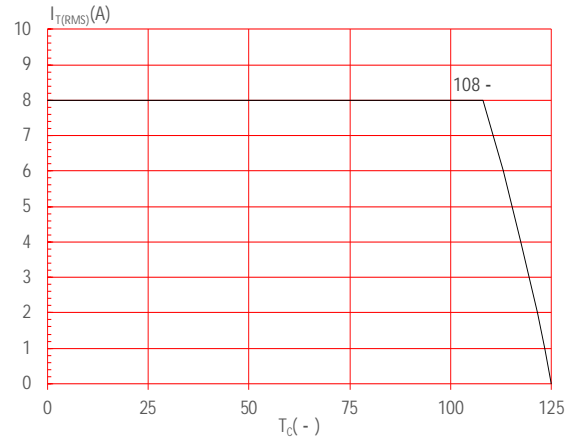


FIG.3: Surge peak on-state current versus number of cycles

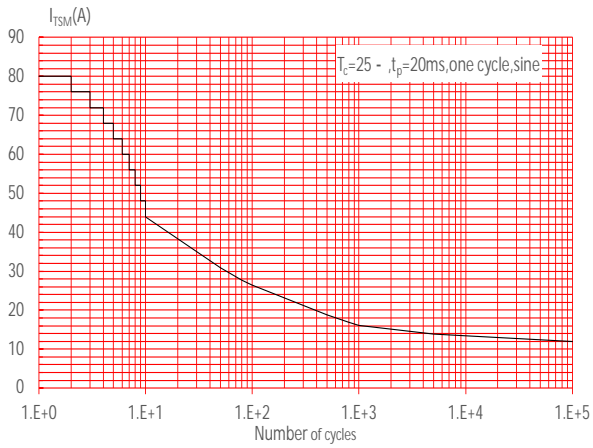


FIG.4: On-state characteristics

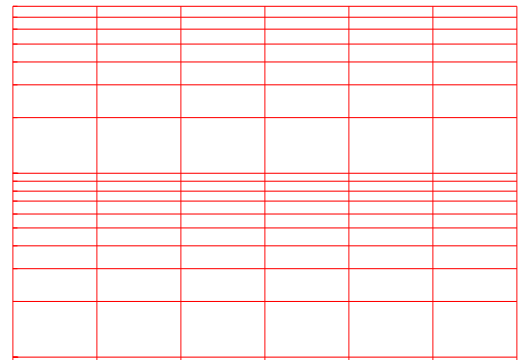
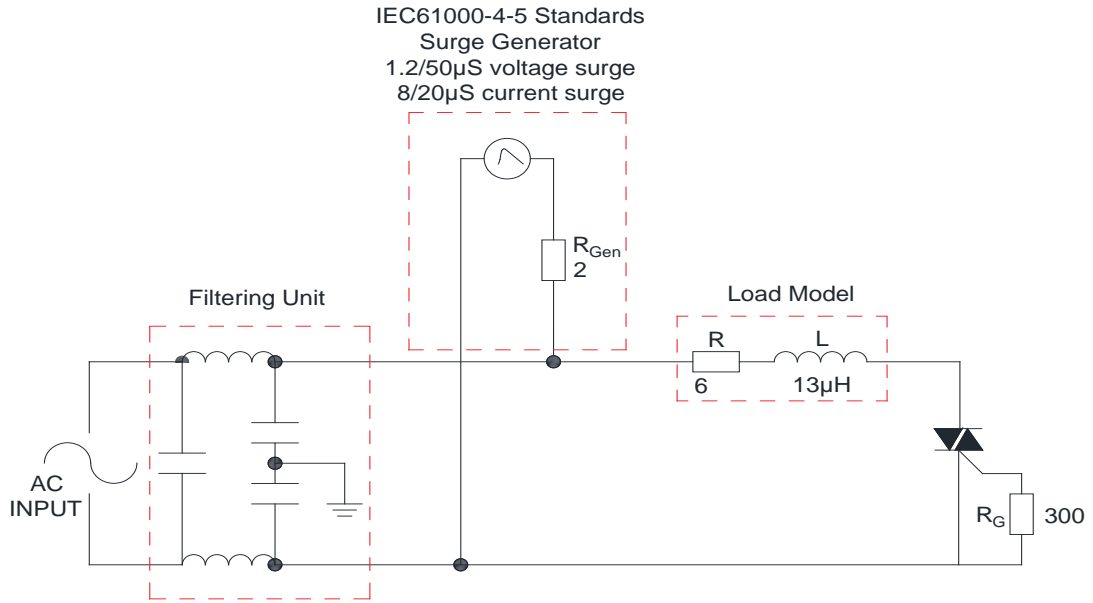


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



JST08C-1200BW



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